



ELECTRONICS, INC.
 44 FARRAND STREET
 BLOOMFIELD, NJ 07003
 (973) 748-5089
<http://www.nteinc.com>

NTE74HC374 Integrated Circuit TTL – High Speed CMOS, Octal D–Type Flip–Flop with 3–State Outputs Common Output Control and Common Clock

Description:

The NTE74HC374 is a high speed octal D–type flip–flop with 3–state outputs in a 20–Lead DIP type package with the capability to drive 15 LS–TTL loads. The eight edge–triggered flip–flops enter data into their registers on the LOW to HIGH transition of clock (CP). The output enable (\overline{OE}) controls the 3–state outputs and is independent of the register operation. When \overline{OE} is HIGH, the outputs are in the high–impedance state.

Features:

- Wide Power Supply Range: 2V to 6V
- High Noise Immunity: $N_{IL} = 30\%$, $N_{IH} = 30\%$ of V_{CC} at $V_{CC} = 5V$
- Buffered Inputs
- Common Three–State Output Enable Control
- Three–State Outputs
- Bus Line Driving Capability
- Typical Propagation Delay (Clock to Q): 15ns at $V_{CC} = 5V$, $C_L = 15pF$, $T_A = +25^\circ C$
- Fanout (Over Temperature Range):
 - Standard Outputs . . . 10 LS–TTL Loads
 - Bus Driver Outputs . . 15 LS–TTL Loads

Absolute Maximum Ratings: (Note 1, Note 2)

Supply Voltage, V_{CC}	–0.5 to +7.0V
Clamp Diode Current, I_{IK} , I_{OK}	±20mA
DC Drain Current (Per Output), I_{OUT}	±35mA
DC Output Source or Sink Current (Per Output), I_{OUT}	±25mA
DC V_{CC} or GND Current (Per Pin), I_{CC}	±50mA
Maximum Junction, T_J	+150°C
Storage Temperature Range, T_{stg}	–65°C to +150°C
Typical Thermal Resistance, Junction–to–Ambient, R_{thJA}	69°C/W
Lead Temperature (During Soldering, 10sec), T_L	+300°C

Note 1. Absolute Maximum Ratings are those values beyond which damage to the device may occur.
 Note 2. Unless otherwise specified, all voltages are referenced to GND.

Recommended Operating Conditions:

Parameter	Symbol	Min	Typ	Max	Unit
Supply Voltage	V_{CC}	2.0	–	6.0	V
DC Input or Output Voltage	V_{IN}, V_{OUT}	0	–	V_{CC}	V
Operating Temperature Range	T_A	–40	–	+85	°C
Input Rise or Fall Times $V_{CC} = 2.0V$	t_r, t_f	–	–	1000	ns
$V_{CC} = 4.5V$		–	–	500	ns
$V_{CC} = 6.0V$		–	–	400	ns

DC Electrical Characteristics:

Parameter	Symbol	Test Conditions	V_{CC}	$T_A = +25^\circ C$		$T_A = -40^\circ \text{ to } +85^\circ C$		Unit
				Typ	Guaranteed Limits			
Minimum HIGH Level Input Voltage	V_{IH}		2.0	–	1.5	1.5	V	
			4.5	–	3.15	3.15	V	
			6.0	–	4.2	4.2	V	
Maximum LOW Level Input Voltage	V_{IL}		2.0	–	0.5	0.5	V	
			4.5	–	1.35	1.35	V	
			6.0	–	1.8	1.8	V	
Minimum HIGH Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OUT} = -20\mu A$	–	V_{CC}	$V_{CC}^{-0.1}$	$V_{CC}^{-0.1}$	V
			$I_{OUT} = -6mA$	4.5	–	3.98	3.84	V
			$I_{OUT} = -7.8mA$	6.0	–	5.48	5.34	V
Minimum LOW Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OUT} = 20\mu A$	–	–	0.1	0.1	V
			$I_{OUT} = 6mA$	4.5	0.2	0.26	0.33	V
			$I_{OUT} = 7.8mA$	6.0	0.2	0.26	0.33	V
Maximum Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	6.0	–	± 0.1	± 1.0	μA	
Maximum Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND, $I_{OUT} = 0\mu A$	6.0	–	8.0	80	μA	
Three-State Leakage Current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL}	6.0	–	± 0.5	± 5.0	μA	

Prerequisite for Switching Specifications:

Parameter	Symbol	Test Conditions	V_{CC}	$T_A = +25^\circ C$		$T_A = -40^\circ \text{ to } +85^\circ C$		Unit
				Typ	Guaranteed Limits			
Maximum Clock Frequency	f_{MAX}		2.0	–	6	5	MHz	
			4.5	–	30	25	MHz	
			6.0	–	35	29	MHz	
Clock Pulse Width	t_W		2.0	–	80	100	ns	
			4.5	–	16	20	ns	
			6.0	–	14	17	ns	
Setup Time (Data to Clock)	t_{SU}		2.0	–	60	75	ns	
			4.5	–	12	15	ns	
			6.0	–	10	13	ns	
Hold Time (Data to Clock)	t_H		2.0	–	5	5	ns	
			4.5	–	5	5	ns	
			6.0	–	5	5	ns	

Switching Specifications: ($t_r = t_f = 6\text{ns}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	V _{CC}	T _A = +25°C		T _A = -40° to +85°C		Unit
				Typ	Guaranteed Limits			
Propagation Delay Time (Clock to Output)	t _{PLH} , t _{PHL}	C _L = 50pF	2.0	-	165	205	ns	
			4.5	-	33	41	ns	
		C _L = 15pF	5.0	15	-	-	ns	
		C _L = 50pF	6.0	-	28	35	ns	
Propagation Delay Time (Disable to Q)	t _{PLZ} , t _{PHZ}	C _L = 50pF	2.0	-	135	170	ns	
			4.5	-	27	34	ns	
		C _L = 15pF	5.0	11	-	-	ns	
		C _L = 50pF	6.0	-	23	29	ns	
Propagation Delay Time (Output Enable to Q)	t _{PZL} , t _{PZH}	C _L = 50pF	2.0	-	150	190	ns	
			4.5	-	30	38	ns	
		C _L = 15pF	5.0	12	-	-	ns	
		C _L = 50pF	6.0	-	26	33	ns	
Maximum Clock Frequency	f _{MAX}	C _L = 15pF	5.0	60	-	-	MHz	
Output Transition Time	t _{TLH} , t _{THL}	C _L = 50pF	2.0	-	60	75	ns	
			4.5	-	12	15	ns	
			6.0	-	10	13	ns	
Maximum Input Capacitance	C _{IN}		-	-	10	10	pF	
Minimum Three-State Output Capacitance	C _O		-	-	20	20	pF	
Power Dissipation Capacitance	C _{PD}	C _L = 15pF, Note 3	5.0	39	-	-	pF	

Note 3. C_{PD} is used to determine the dynamic power consumption, per channel.
 $P_D = C_{PD} V_{CC}^2 f_i + \sum V_{CC}^2 f_o C_L$ where f_i = Input Frequency, f_o = Output Frequency,
 C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Truth Table:

Inputs			Output
\overline{OE}	CP	Data D _n	Q _n
L	↑	H	H
L	↑	L	L
L	L	X	Q0
H	X	X	Z

H = HIGH Level (Steady State)

L = LOW Level (Steady State)

X = Don't Care

↑ = Transition from LOW to HIGH Level

Q0 = The level of Q before the indicated steady state input conditions were established.

Z = High Impedance State

Pin Connection Diagram

